

2N6487, 2N6488, (NPN) 2N6490, 2N6491 (PNP)

2N6488 and 2N6491 are Preferred Devices

Complementary Silicon Plastic Power Transistors

These devices are designed for use in general-purpose amplifier and switching applications.

Features

- DC Current Gain Specified to 15 Amperes -
 $h_{FE} = 20 - 150 @ I_C = 5.0 \text{ Adc}$
 $= 5.0 (\text{Min}) @ I_C = 15 \text{ Adc}$
- Collector-Emitter Sustaining Voltage -
 $V_{CEO(\text{sus})} = 60 \text{ Vdc (Min) - 2N6487, 2N6490}$
 $= 80 \text{ Vdc (Min) - 2N6488, 2N6491}$
- High Current Gain - Bandwidth Product
 $f_T = 5.0 \text{ MHz (Min) @ } I_C = 1.0 \text{ Adc}$
- TO-220AB Compact Package
- Pb-Free Packages are Available*

MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage 2N6487, 2N6490 2N6488, 2N6491	V_{CEO}	60 80	Vdc
Collector-Base Voltage 2N6487, 2N6490 2N6488, 2N6491	V_{CB}	70 90	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current - Continuous	I_C	15	Adc
Base Current	I_B	5.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	75 0.6	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.8 0.014	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.67	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	70	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates JEDEC Registered Data.

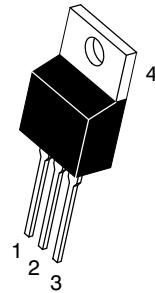
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

15 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60-80 VOLTS, 75 WATTS

MARKING DIAGRAM



TO-220AB
CASE 221A
STYLE 1



2N64xx = Specific Device Code
 xx = See Table on Page 5
 G = Pb-Free Package
 A = Assembly Location
 Y = Year
 WW = Work Week

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

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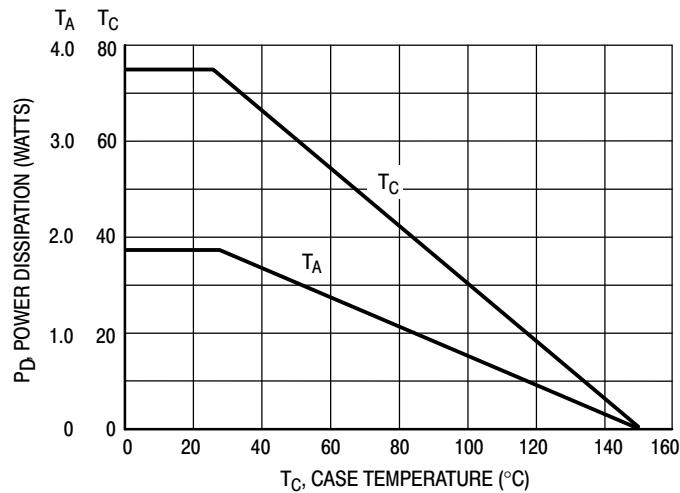


Figure 1. Power Derating

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted) (Note 2)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (Note 3) ($I_C = 200\text{ mAdc}$, $I_B = 0$)	$V_{CEO(sus)}$	60 80	- -	Vdc
Collector-Emitter Sustaining Voltage (Note) ($I_C = 200\text{ mAdc}$, $V_{BE} = 1.5\text{ Vdc}$)	V_{CEX}	70 90	- -	Vdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 40\text{ Vdc}$, $I_B = 0$)	I_{CEO}	- -	1.0 1.0	mAdc
Collector Cutoff Current ($V_{CE} = 65\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$) ($V_{CE} = 85\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$) ($V_{CE} = 60\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$) ($V_{CE} = 80\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$)	I_{CEX}	- - - -	500 500 5.0 5.0	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	-	1.0	mAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 5.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 15\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	h_{FE}	20 5.0	150 -	-
Collector-Emitter Saturation Voltage ($I_C = 5.0\text{ Adc}$, $I_B = 0.5\text{ Adc}$) ($I_C = 15\text{ Adc}$, $I_B = 5.0\text{ Adc}$)	$V_{CE(sat)}$	- -	1.3 3.5	Vdc
Base-Emitter On Voltage ($I_C = 5.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 15\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	$V_{BE(on)}$	- -	1.3 3.5	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain - Bandwidth Product (Note 4) ($I_C = 1.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$, $f_{test} = 1.0\text{ MHz}$)	f_T	5.0	-	MHz
Small-Signal Current Gain ($I_C = 1.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	25	-	-

2. Indicates JEDEC Registered Data.

3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

4. $f_T = |h_{fe}| \cdot f_{test}$

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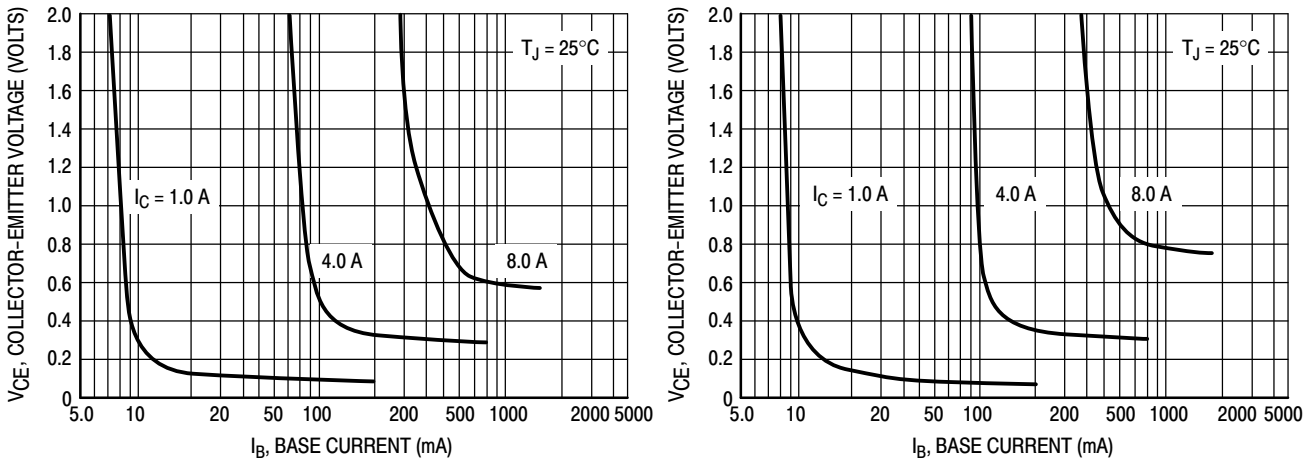


Figure 9. Collector Saturation Region

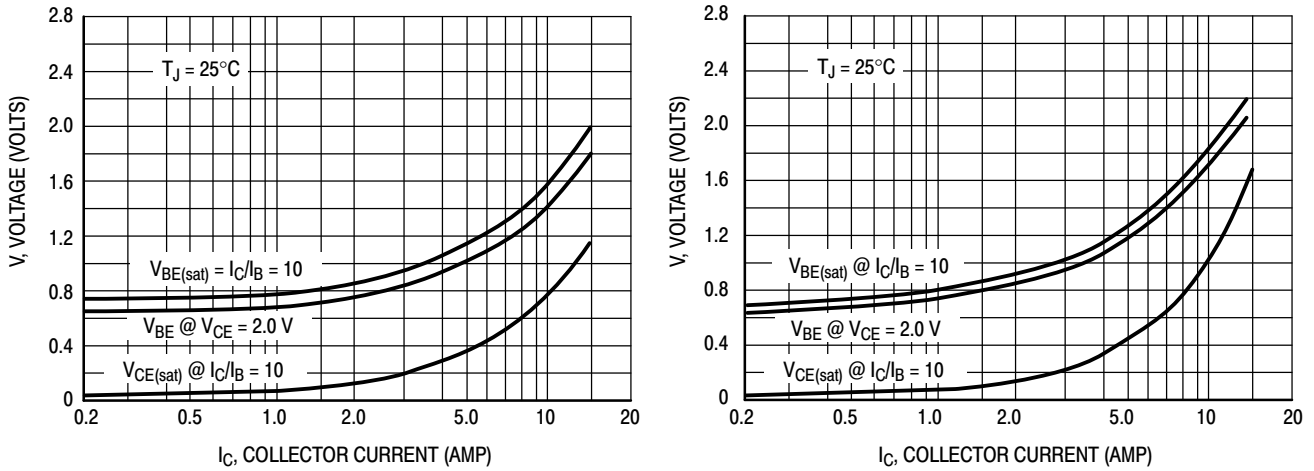


Figure 10. "On" Voltages

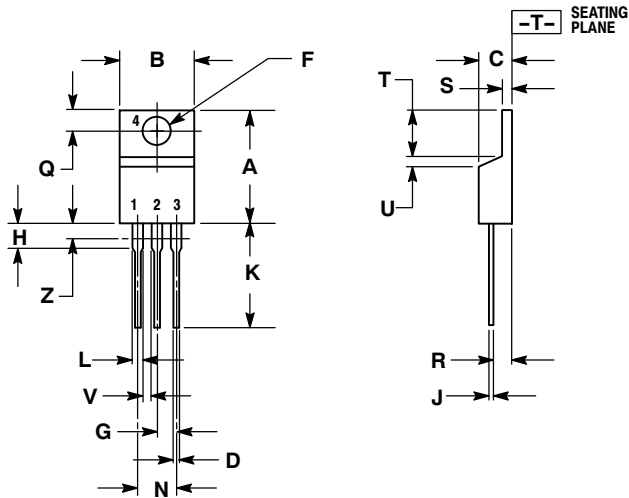
ORDERING INFORMATION

Device	Device Marking	Package	Shipping
2N6487	2N6487	TO-220AB	50 Units / Rail
2N6487G		TO-220AB (Pb-Free)	
2N6488	2N6488	TO-220AB	50 Units / Rail
2N6488G		TO-220AB (Pb-Free)	
2N6490	2N6490	TO-220AB	50 Units / Rail
2N6490G		TO-220AB (Pb-Free)	
2N6491	2N6491	TO-220AB	50 Units / Rail
2N6491G		TO-220AB (Pb-Free)	

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PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AE



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04